

- ★ Green Device Available
- ★ Super Low Gate Charge
- ★ Excellent CdV/dt effect decline
- ★ Advanced high cell density Trench technology

Product Summary

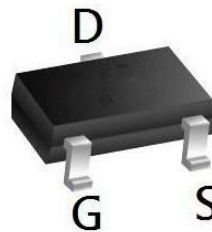
BVDSS	RDSON	ID
-30V	16mΩ	-9.0A

Description

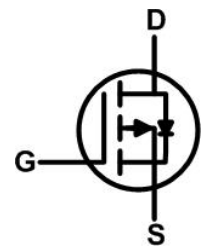
The RST30P09 is the high cell density trenched P-ch MOSFETS, which provide excellent RDSON and gate charge for most of the synchronous buck converter applications.

The RST30P09 meet the RoHS and Green Product requirement

SOT23-3 Pin Configuration



pin assignment



Schematic diagram

Package Marking and Ordering Information

Product	Package	Marking	Packing	Min Unit Quantity
RST30P09	SOT23-3	*	3000PCS/Reel	3000PCS

Absolute Maximum Ratings (TA=25°C unless otherwise specified)

Symbol	Parameter		Max.	Units
V _{DSS}	Drain-Source Voltage		-30	V
V _{GSS}	Gate-Source Voltage		±20	V
I _D	Continuous Drain Current	T _A = 25°C	-9	A
		T _A = 100°C	-5.0	A
I _{DM}	Pulsed Drain Current ^{note1}		-36	A
E _{AS}	Single Pulsed Avalanche Energy ^{note2}		25	mJ
P _D	Power Dissipation	T _A = 25°C	3.0	W
R _{θJA}	Thermal Resistance, Junction to Ambient		48	°C/W
T _J , T _{STG}	Operating and Storage Temperature Range		-55 to +150	°C

Electrical Characteristics (T_J=25°C unless otherwise specified)

Symbol	Parameter	Test Condition	Min.	Typ.	Max.	Units
Off Characteristic						
V _{(BR)DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D = -250μA	-30	-	-	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{DS} = -30V, V _{GS} = 0V,	-	-	-1	μA
I _{GSS}	Gate to Body Leakage Current	V _{DS} =0V, V _{GS} = ±20V	-	-	±100	nA
On Characteristics						
V _{GS(th)}	Gate Threshold Voltage	V _{DS} = V _{GS} , I _D = -250μA	-1.0	-1.5	-2.5	V
R _{DS(on)}	Static Drain-Source on-Resistance Note3	V _{GS} =-10V, I _D =-10A	-	16	18	mΩ
		V _{GS} =-4.5V, I _D =-5A	-	20	23	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} = -15V, V _{GS} = 0V, f = 1.0MHz	-	900	-	pF
C _{oss}	Output Capacitance		-	125	-	pF
C _{rss}	Reverse Transfer Capacitance		-	109	-	pF
Q _g	Total Gate Charge	V _{DS} = -15V, I _D = -8A, V _{GS} = -10V	-	42	-	nC
Q _{gs}	Gate-Source Charge		-	8.8	-	nC
Q _{gd}	Gate-Drain(“Miller”) Charge		-	7.3	-	nC
Switching Characteristics						
t _{d(on)}	Turn-on Delay Time	V _{DD} = -15V, I _D = -1A, V _{GS} =-10V, R _{GEN} =6Ω	-	13	-	ns
t _r	Turn-on Rise Time		-	15	-	ns
t _{d(off)}	Turn-off Delay Time		-	198	-	ns
t _f	Turn-off Fall Time		-	98	-	ns
Drain-Source Diode Characteristics and Maximum Ratings						
I _S	Maximum Continuous Drain to Source Diode Forward Current		-	-	-9	A
I _{SM}	Maximum Pulsed Drain to Source Diode Forward Current		-	-	-36	A
V _{SD}	Drain to Source Diode Forward Voltage	V _{GS} = 0V, I _S = -9A	-	-0.8	-1.2	V

Notes:1. Repetitive Rating: Pulse Width Limited by Maximum Junction Temperature

2. EAS condition: T_J=25°C, V_{DD}=-15V, V_G=-10V, R_G=25Ω, L=0.5mH, I_{AS}=-10A

3. Pulse Test: Pulse Width≤300μs, Duty Cycle≤2%

Typical Performance Characteristics

Figure 1: Output Characteristics

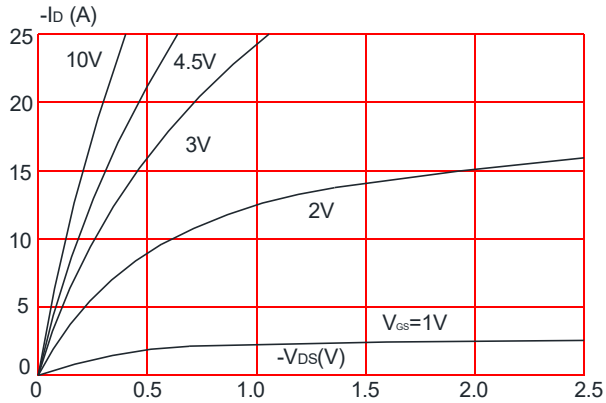


Figure 2: Typical Transfer Characteristics

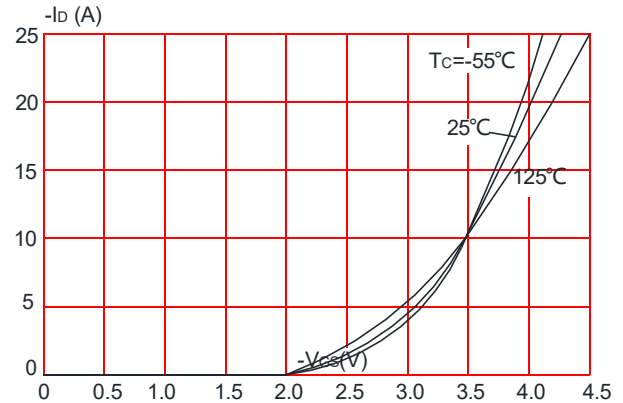


Figure 3: On-resistance vs. Drain Current

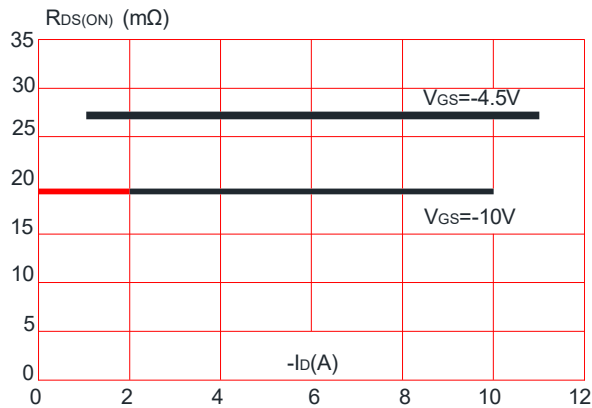


Figure 4: Body Diode Characteristics

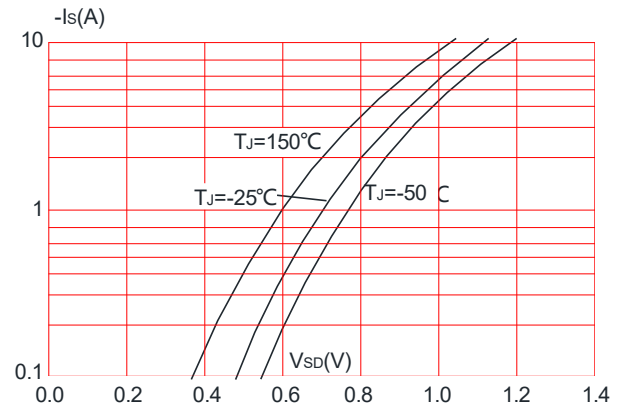


Figure 5: Gate Charge Characteristics

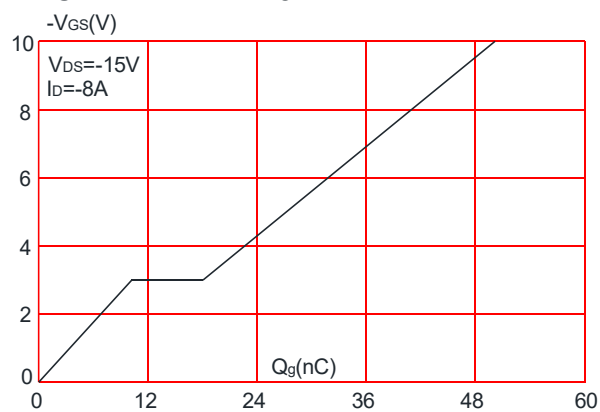


Figure 6: Capacitance Characteristics

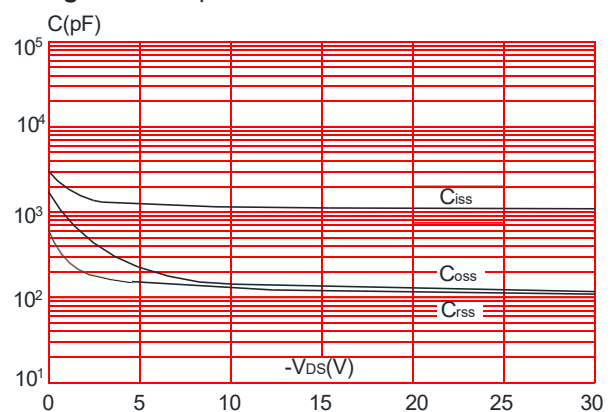


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

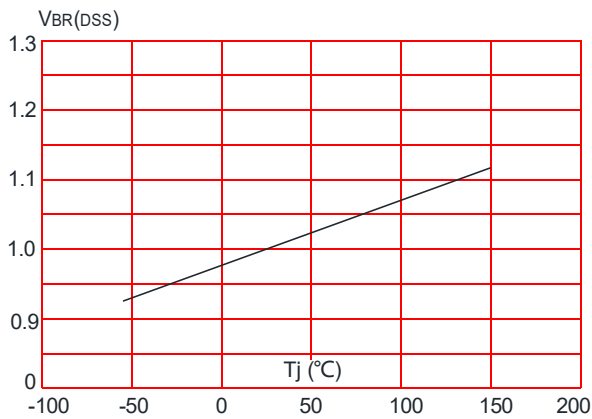


Figure 8: Normalized on Resistance vs. Junction Temperature

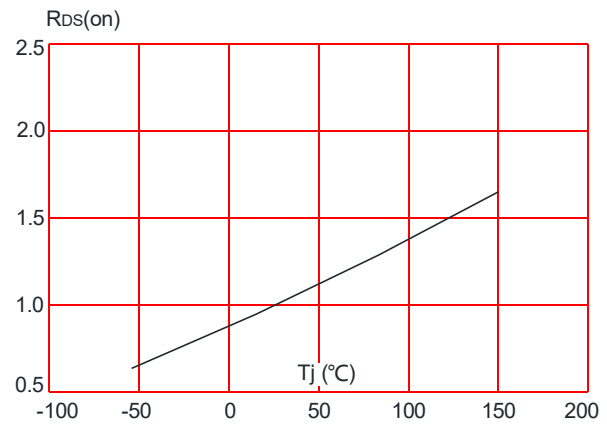


Figure 9: Maximum Safe Operating Area

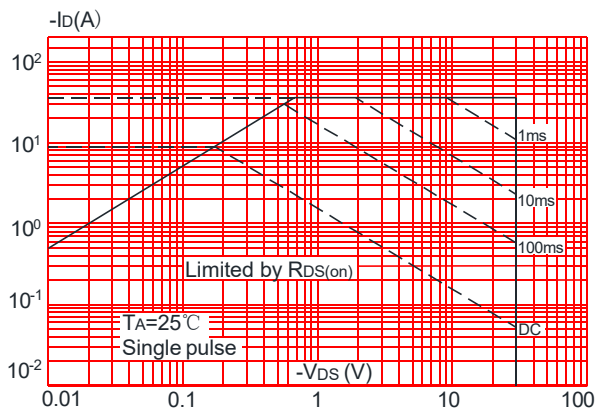


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

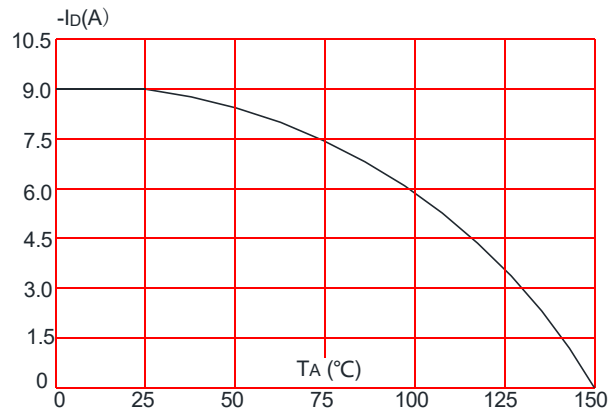
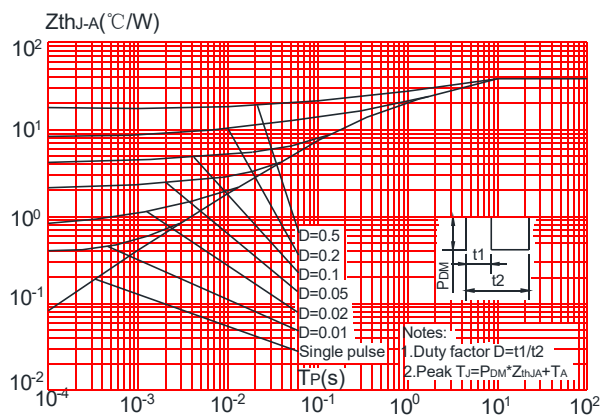
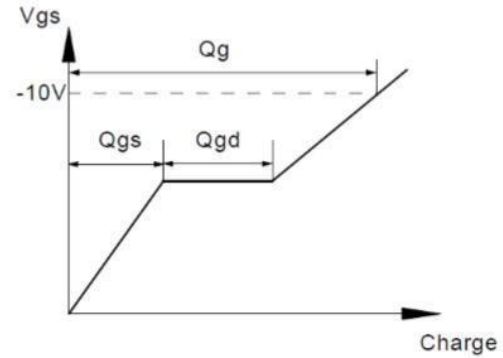
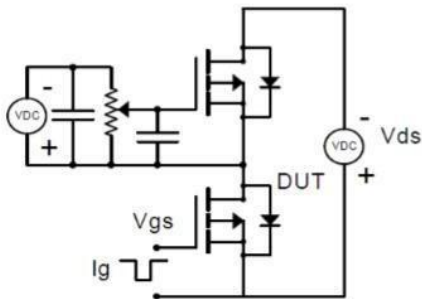


Figure.11: Maximum Effective Transient Thermal Impedance, Junction-to-Ambient

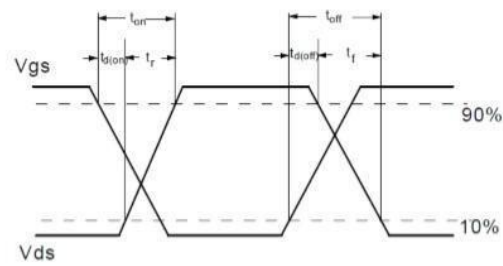
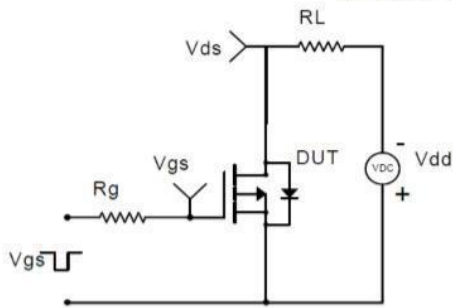


Test Circuit

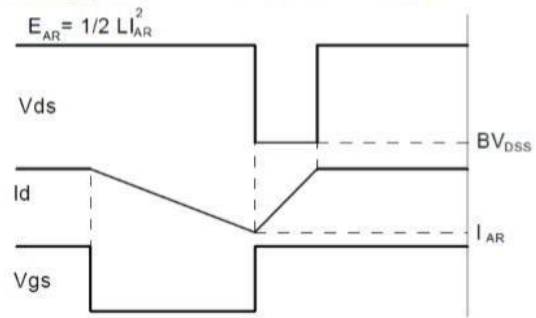
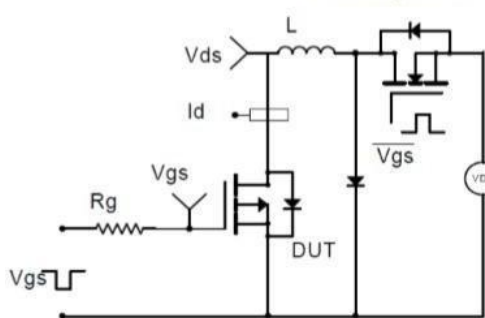
Gate Charge Test Circuit & Waveform



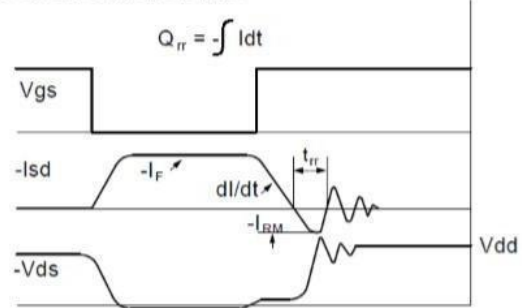
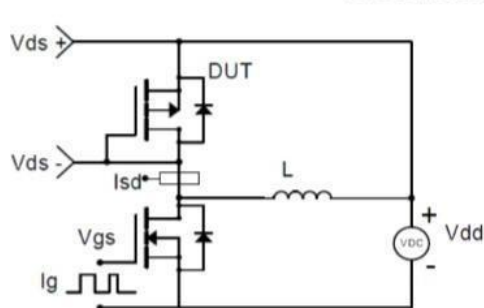
Resistive Switching Test Circuit & Waveforms



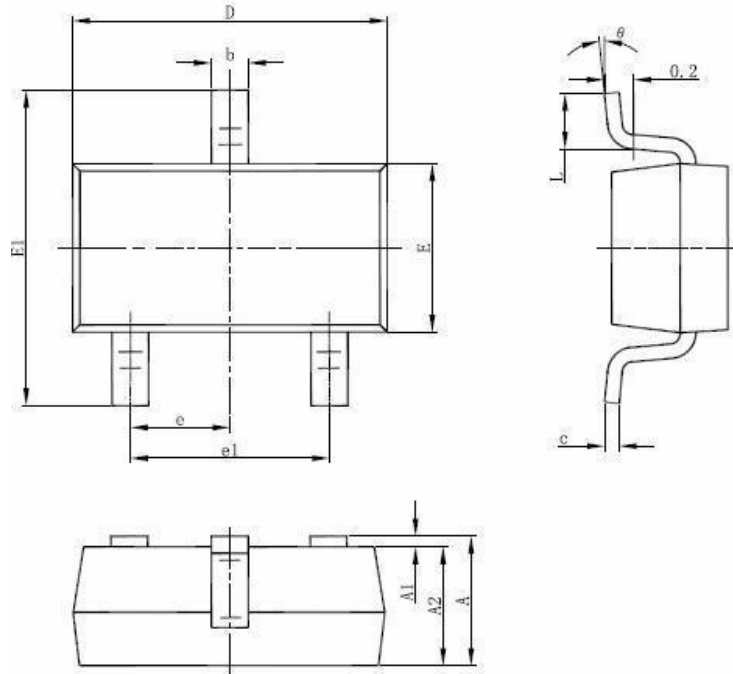
Unclamped Inductive Switching (UIS) Test Circuit & Waveforms



Diode Recovery Test Circuit & Waveforms



SOT-23-3L Package Information



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min	Max	Min	Max
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
c	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E	1.500	1.700	0.059	0.067
E1	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°